

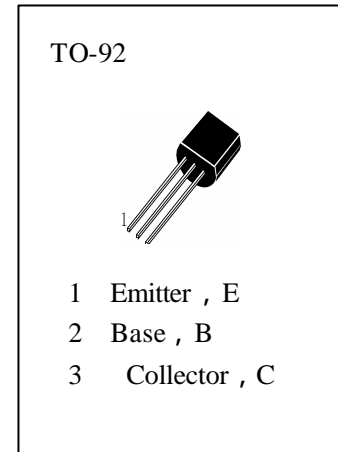


APPLICATIONS

The H945 is designed for driver stage of AF amplifier
And low speed switching.

ABSOLUTE MAXIMUM RATINGS ($T_a=25$)

- T_{stg} —Storage Temperature..... -55~150
- T_j —Junction Temperature.....150
- P_C —Collector Dissipation.....250mW
- V_{CBO} —Collector-Base Voltage.....60V
- V_{CEO} —Collector-Emitter Voltage.....50V
- V_{EBO} —Emitter-Base Voltage.....5V
- I_C —Collector Current.....150mA



ELECTRICAL CHARACTERISTICS ($T_a=25$)

Symbol	Characteristics	Min	Typ	Max	Unit	Test Conditions
BVCBO	Collector-Base Breakdown Voltage	60			V	$I_C=100 \mu A, I_E=0$
BVCEO	Collector-Emitter Breakdown Voltage	50			V	$I_C=100 \mu A, I_B=0$
BVEBO	Emitter-Base Breakdown Voltage	5			V	$I_E=100 \mu A, I_C=0$
h_{FE}	DC Current Gain	70		700		$V_{CE}=6V, I_C=1mA$
$V_{CE(sat)}$	Collector- Emitter Saturation Voltage			0.3	V	$I_C=100mA, I_B=10mA$
$V_{BE(sat)}$	Base-Emitter Saturation Voltage			1.0	V	$I_C=100mA, I_B=10mA$
I_{CBO}	Collector Cut-off Current			100	nA	$V_{CB}=60V, I_E=0$
I_{EBO}	Emitter Cut-off Current			100	nA	$V_{EB}=5V, I_C=0$
f_T	Current Gain-Bandwidth Product		300		MHz	$V_{CE}=6V, I_C=10mA$
C_{ob}	Output Capacitance		2.5		pF	$V_{CB}=6V, I_E=0, f=1MHz$
NF	Noise Figure		4.0		dB	$V_{CE}=6V, I_C=0.5mA, f=1KHz, R_S=500$

h_{FE} Classification

O	Y	GR	BL
70—140	120—240	200—400	350—700